

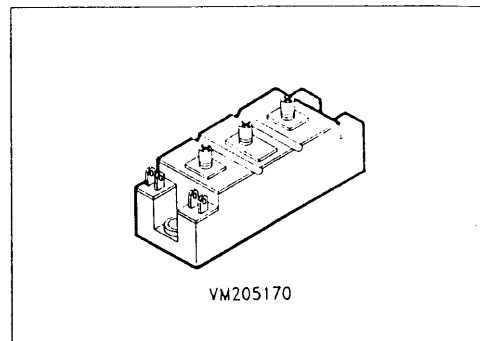
877-311

IGBT Module Preliminary Data

BSM 75 GB 100 D
BSM 75 GAL 100 D

$V_{CE} = 1000 \text{ V}$
 $I_C = 2 \times 75 \text{ A} / 1 \times 75 \text{ A}$

- Power module
- Half-bridge / Chopper
- Including fast free-wheel diodes
- Package with insulated metal base plate
- Package outline / Circuit diagram: 2b, 2c¹⁾



Half-bridge		Chopper	
Type	Ordering Code	Type	Ordering Code
BSM 75 GB 100 D	C67076-A2104-A2	BSM 75 GAL 100 D	C67076-A2003-A2

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1000	V
Collector-gate voltage, $R_{GE} = 20 \text{ k}\Omega$	V_{CGR}	1000	
Gate-emitter voltage	V_{GE}	± 20	
Continuous collector current, $T_C = 80 \text{ }^\circ\text{C}$	I_C	75	A
Pulsed collector current, $T_C = 80 \text{ }^\circ\text{C}$	$I_{C \text{ puls}}$	150	
Operating and storage temperature range	T_j T_{stg}	$-55 \dots +150$	$^\circ\text{C}$
Power dissipation, $T_C = 25 \text{ }^\circ\text{C}$	P_{tot}	625	W
Thermal resistance Chip - case	$R_{th \text{ JC}}$	≤ 0.2	K/W
Insulation test voltage ²⁾ , $t = 1 \text{ min.}$	V_{is}	2500	V_{ac}
Creepage distance	—	16	mm
Clearance	—	11	
DIN humidity category, DIN 40 040	—	F	—
IEC climatic category, DIN IEC 68-1	—	55/150/56	

¹⁾ See chapter Package Outlines and Circuit Diagrams

²⁾ Insulation test voltage between collector and base plate referred to standard climate 23/50 in acc. with DIN 50 014, IEC 146, para. 492.1.

Electrical Characteristics

at $T_j = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static characteristics

Collector-emitter breakdown voltage $V_{GE} = 0, I_C = 1.4\text{ mA}$	$V_{(BR)CES}$	1000	—	—	V
Gate threshold voltage $V_{GE} = V_{CE}, I_C = 5\text{ mA}$	$V_{GE(th)}$	4.5	5.5	6.5	
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 75\text{ A}$ $T_j = 25\text{ °C}$ $T_j = 150\text{ °C}$	$V_{CE(sat)}$	— —	2.8 4.0	3.3 4.5	
Zero gate voltage collector current $V_{CE} = 1000\text{ V}, V_{GE} = 0$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	I_{CES}	— —	— —	1400 —	μA
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0$	I_{GES}	—	—	100	nA

AC characteristics

Forward transconductance $V_{CE} = 20\text{ V}, I_C = 75\text{ A}$	g_{fs}	27	40	—	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	C_{iss}	—	11000	14600	pF
Output capacitance, $V_{GS} = 0$, $V_{CE} = 25\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	C_{oss}	—	850	—	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	C_{rss}	—	350	—	

Switching Characteristics
at $T_j = 125\text{ }^{\circ}\text{C}$

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Resistive load

Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	$t_{d(on)}$	—	130	—	ns
Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	t_r	—	400	—	
Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	$t_{d(off)}$	—	300	—	
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	t_f	—	400	—	

Inductive load

Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	$t_{d(off)}$	—	300	—	ns
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	t_f	—	200	—	
Turn-off loss ($E_{off} = E_{off1} + E_{off2}$) $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{g(on)} = 3.3\text{ }\Omega$, $R_{g(off)} = 3.3\text{ }\Omega$	E_{off1} E_{off2}	— —	4.5 3.5	— —	mWs

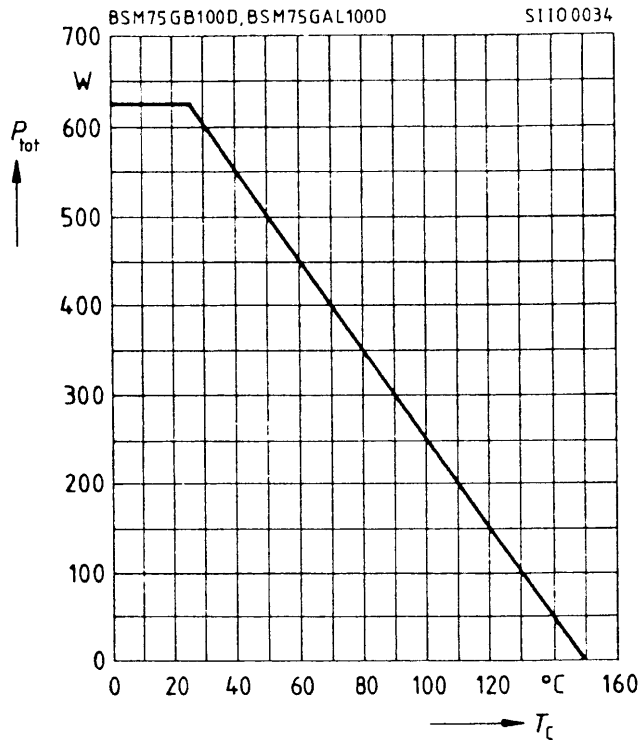
Electrical Characteristics (continued)
at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Free-wheel diode					
Diode forward voltage $I_F = 75\text{ A}$, $V_{GE} = 0$ $T_j = 25\text{ }^{\circ}\text{C}$ $T_j = 125\text{ }^{\circ}\text{C}$	V_F	— —	1.8 1.6	2.5 —	V
Reverse recovery time $I_F = 75\text{ A}$, $V_R = 600\text{ V}$ $V_{GE} = 0$, $di_F/dt = -800\text{ A}/\mu\text{s}$ $T_j = 125\text{ }^{\circ}\text{C}$	t_{rr}	—	0.25	—	μs
Reverse recovery charge $I_F = 75\text{ A}$, $V_R = 600\text{ V}$ $V_{GE} = 0$, $di_F/dt = -800\text{ A}/\mu\text{s}$ $T_j = 25\text{ }^{\circ}\text{C}$ $T_j = 125\text{ }^{\circ}\text{C}$	Q_{rr}	— —	3 13.5	— —	μC
Soft factor $I_F = 75\text{ A}$, $V_R = 600\text{ V}$ $V_{GE} = 0$, $di_F/dt = -800\text{ A}/\mu\text{s}$ $T_j = 125\text{ }^{\circ}\text{C}$	S	—	1	—	—
Thermal resistance Chip - case	R_{thJC}	—	—	0.75	K/W

Characteristics at $T_j = 25^\circ\text{C}$, unless otherwise specified.

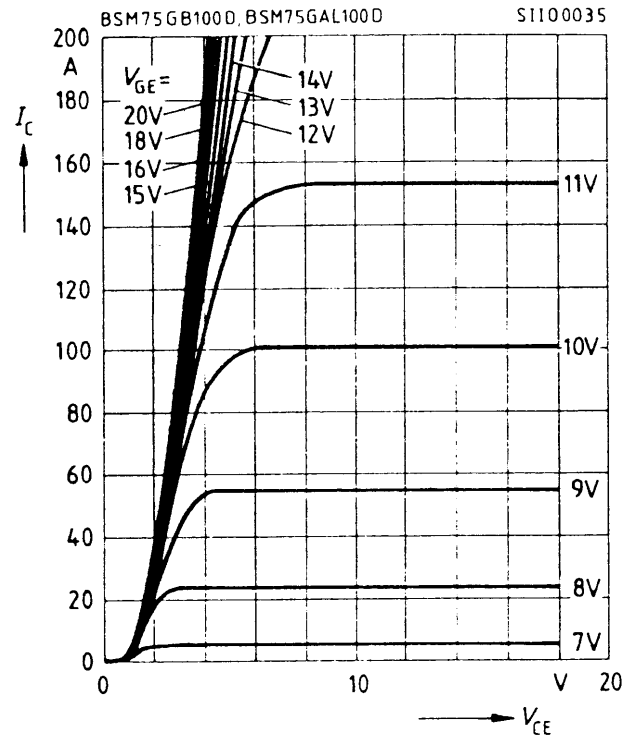
Power dissipation $P_{\text{tot}} = f(T_c)$

parameter: $T_j = 150^\circ\text{C}$



Typ. output characteristics $I_C = f(V_{CE})$

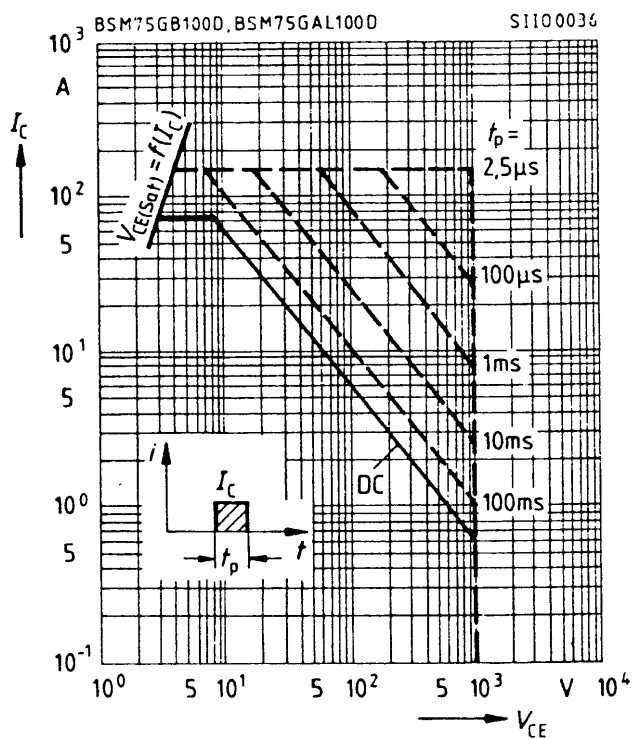
parameter: $t_p = 80\ \mu\text{s}$



Safe operating area $I_C = f(V_{CE})$

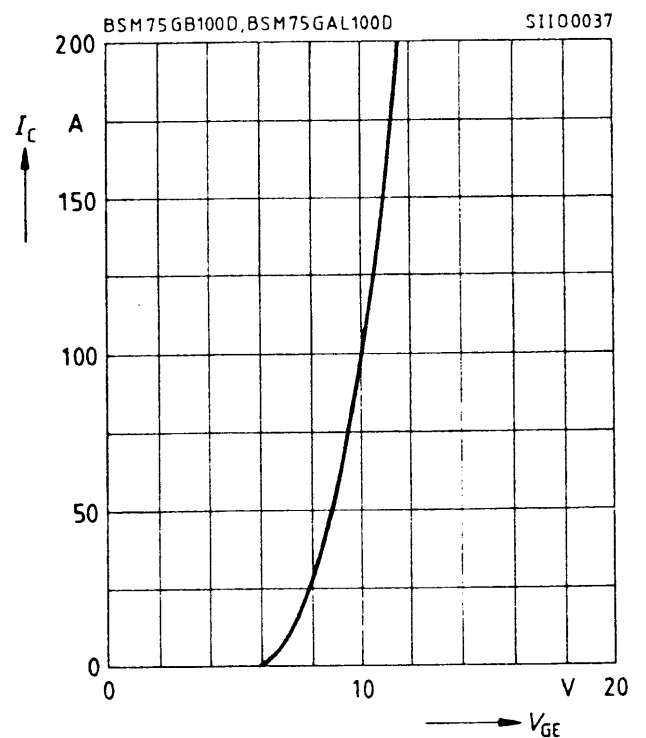
parameter: single pulse, $T_c = 25^\circ\text{C}$

$T_j \leq 150^\circ\text{C}$



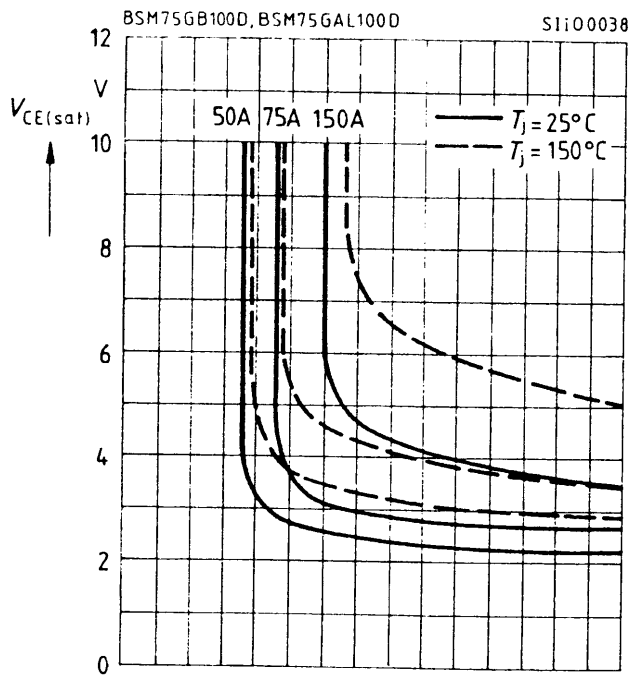
Typ. transfer characteristics $I_C = f(V_{GE})$

parameter: $t_p = 80\ \mu\text{s}$, $V_{CE} = 20\ \text{V}$



Typ. on-state characteristics

$V_{CE(sat)} = f(V_{GE})$, parameter: I_C , T_j



Collector current $I_C = f(T_C)$

parameter: $V_{GE} \geq 15$ V, $T_i = 150$ °C

